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L Number	Hits	Search Text	DB	Time stamp
1	308467	sulfuric near acid or "H.sub.2 SO.sub.4" and phosphoric near acid or "H.sub.3 PO.sub.4" and hydrofluoric near acid or "HF"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 18:25
2	5653	(sulfuric near acid or "H.sub.2 SO.sub.4" and phosphoric near acid or "H.sub.3 PO.sub.4" and hydrofluoric near acid or "HF") and ((etch\$3 or planariz\$3) same (silicon near oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:44
3	3748	((sulfuric near acid or "H.sub.2 SO.sub.4" and phosphoric near acid or "H.sub.3 PO.sub.4" and hydrofluoric near acid or "HF") and ((etch\$3 or planariz\$3) same (silicon near oxide))) and @pd<20020207	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:46
4	102	((((sulfuric near acid or "H.sub.2 SO.sub.4" and phosphoric near acid or "H.sub.3 PO.sub.4" and hydrofluoric near acid or "HF") and ((etch\$3 or planariz\$3) same (silicon near oxide))) and @pd<20020207) and 438/723-733.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:50
5	0	((((sulfuric near acid or "H.sub.2 SO.sub.4" and phosphoric near acid or "H.sub.3 PO.sub.4" and hydrofluoric near acid or "HF") and ((etch\$3 or planariz\$3) same (silicon near oxide))) and @pd<20020207) and (438/723 and 438/733).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:51
6	62	((((sulfuric near acid or "H.sub.2 SO.sub.4" and phosphoric near acid or "H.sub.3 PO.sub.4" and hydrofluoric near acid or "HF") and ((etch\$3 or planariz\$3) same (silicon near oxide))) and @pd<20020207) and (438/723).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:52
7	4	((((sulfuric near acid or "H.sub.2 SO.sub.4" and phosphoric near acid or "H.sub.3 PO.sub.4" and hydrofluoric near acid or "HF") and ((etch\$3 or planariz\$3) same (silicon near oxide))) and @pd<20020207) and (438/733).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:52
8	6523	(sulfuric near acid or "H.sub.2 SO.sub.4") and (phosphoric near acid or "H.sub.3 PO.sub.4") and (hydrofluoric near acid or "HF")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 18:51
9	236	((sulfuric near acid or "H.sub.2 SO.sub.4") and (phosphoric near acid or "H.sub.3 PO.sub.4") and (hydrofluoric near acid or "HF")) and ((etch\$3 or planariz\$3) same (silicon near oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 16:57
11	0	(((((sulfuric near acid or "H.sub.2 SO.sub.4") and (phosphoric near acid or "H.sub.3 PO.sub.4") and (hydrofluoric near acid or "HF")) and ((etch\$3 or planariz\$3) same (silicon near oxide))) and @pd<20020207) and (anisotropic near etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 17:04
10	116	((((sulfuric near acid or "H.sub.2 SO.sub.4") and (phosphoric near acid or "H.sub.3 PO.sub.4") and (hydrofluoric near acid or "HF")) and ((etch\$3 or planariz\$3) same (silicon near oxide))) and @pd<20020207	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 17:04
12	801	(polish\$3 or planariz\$3 or etch\$3) same (inter near metallic near dielectric or "IMD")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 18:29
13	7	((polish\$3 or planariz\$3 or etch\$3) same (inter near metallic near dielectric or "IMD")) and ((sulfuric near acid or "H.sub.2 SO.sub.4") and (phosphoric near acid or "H.sub.3 PO.sub.4") and (hydrofluoric near acid or "HF"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 18:34

32	((sulfuric near acid or "H.sub.2 SO.sub.4") and (phosphoric near acid or "H.sub.3 PO.sub.4") and (hydrofluoric near acid or "HF")) and 252/79.1.ccls.
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